



GP
ELECTRONICS

GPT022N03FDA
30V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	1.5mΩ@10V	90A
	3.0mΩ@4.5V	

Feature

- Split Gate Trench technology
- Excellent gate charge × $R_{DS(on)}$ product
- Excellent package for good heat dissipation

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

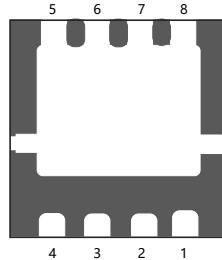
MARKING:



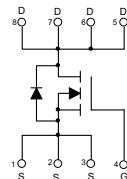
T022N03 = Device code

XX = Date Code

PLP3.3×3.3-8L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

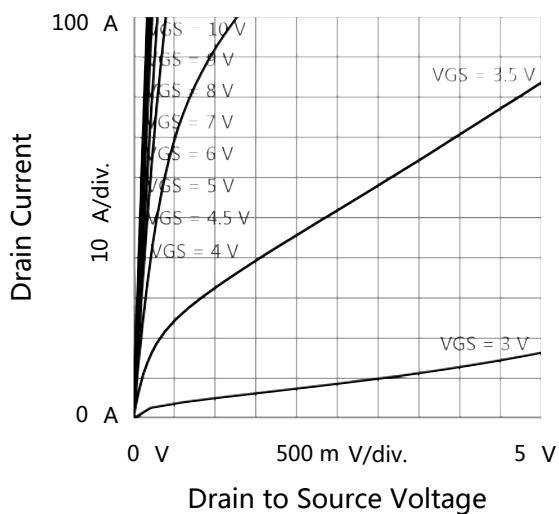
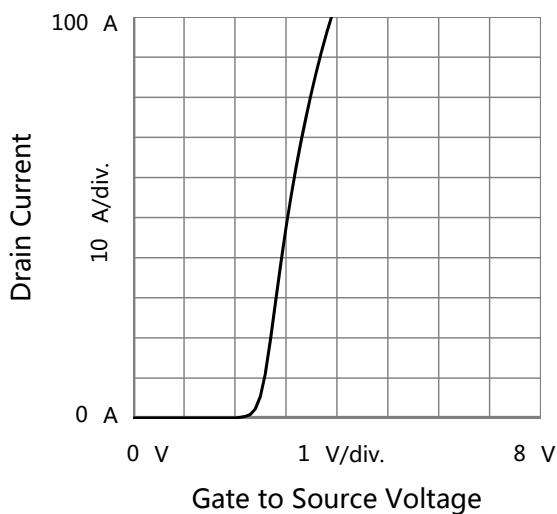
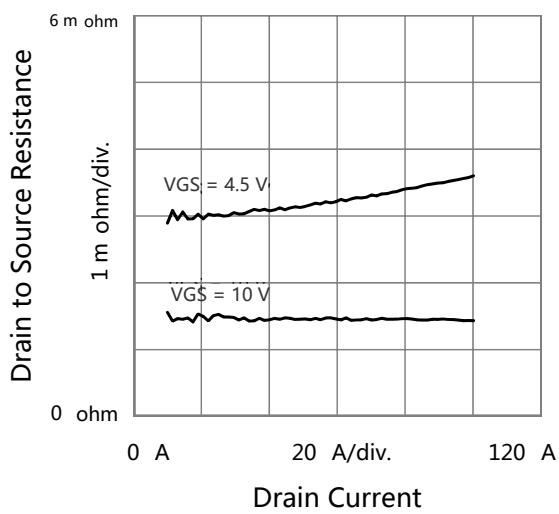
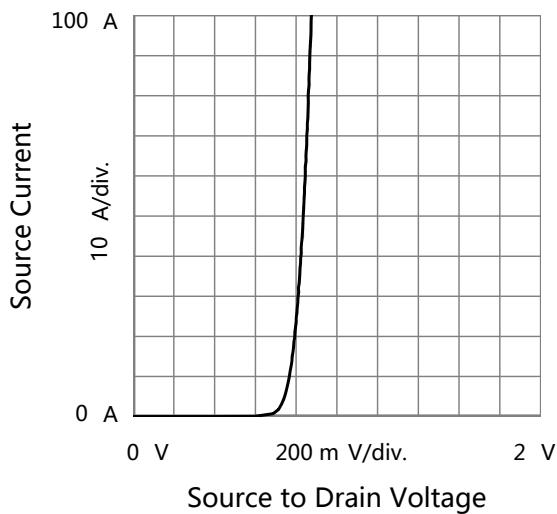
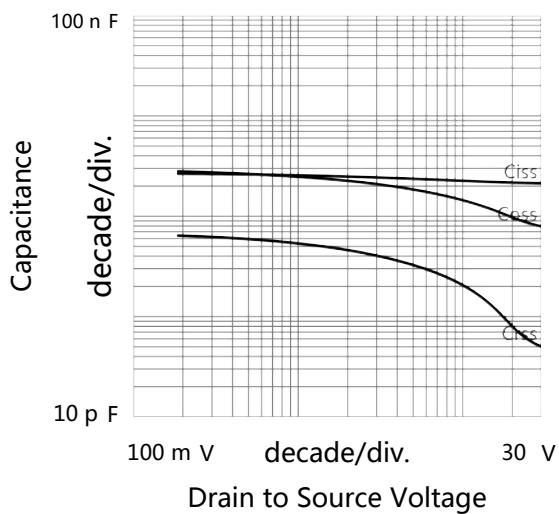
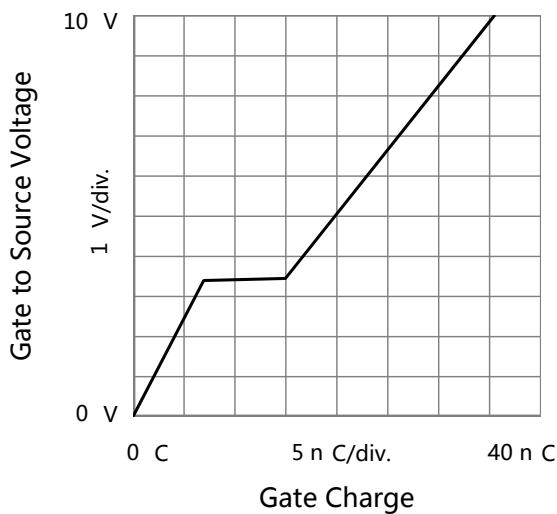
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁴	I_D	90	A
Pulsed Drain Current ³	I_{DM}	400	A
Avalanche Current ¹	I_{AS}	27	A
Single Pulse Avalanche Energy ¹	E_{AS}	182	mJ
Power Dissipation ²	P_D	83	W
Thermal Resistance from Junction to Case	Steady-State	1.5	$^\circ\text{C}/\text{W}$
Junction Temperature		150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 24\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
On Characteristics⁵						
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1	2	3	V
Drain-source on-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 15\text{A}$		1.5	2.2	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_D = 10\text{A}$		3.0	4.8	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_D = 10\text{A}$				S
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		2190		pF
Output capacitance	C_{oss}			1200		
Reverse transfer capacitance	C_{rss}			153		
Switching Characteristics						
Total gate charge	Q_g	$V_{\text{DS}} = 15\text{V}, I_D = 35\text{A}, V_{\text{GS}} = 10\text{V}$		39.2		nC
Gate-source charge	Q_{gs}			5.9		
Gate-drain charge	Q_{gd}			6.3		
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 15\text{V}, I_D = 35\text{A}, V_{\text{GS}} = 10\text{V}, R_G = 1.6\Omega$		4.9		ns
Turn-on rise time	t_r			6.9		
Turn-off delay time	$t_{\text{d}(\text{off})}$			25		
Turn-off fall time	t_f			4.8		
Diode Characteristics						
Diode Forward Voltage ⁵	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = 10\text{A}$		0.76	1.2	V
Maximum Diode Continuous Current ⁴	I_{SM}				300	A

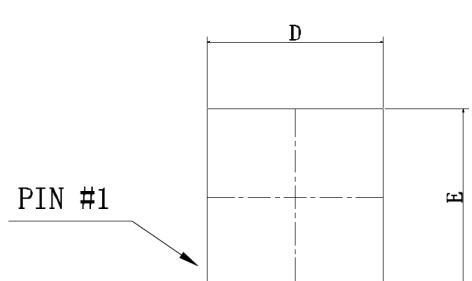
Notes :

- 1.EAS condition: $V_{\text{DD}} = 15\text{V}, V_{\text{GS}} = 10\text{V}, L = 0.5\text{mH}, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 2.The power dissipation P_D is based on $T_{J(\text{MAX})} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- 3.Single pulse width limited by junction temperature $T_{J(\text{MAX})} = 150^\circ\text{C}$.
- 4.The maximum current rating is package limited.
- 5.The static characteristics are obtained using <380ms pulses, duty cycle 2% max

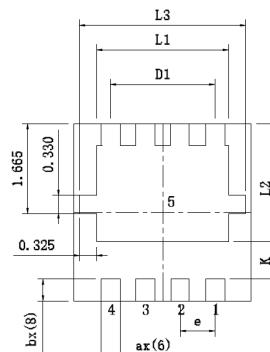
Typical Electrical and Thermal Characteristics
Output Characteristics

Transfer Characteristics

Drain to Source Resistance vs. Drain Current

Body Diode Forward Characteristics

Capacitances

Gate Charge


PLP3.3×3.3-8L Package Information

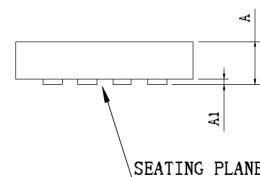
symbol	Dimension in mm		
	MIN	NOM	MAX
A	0.650	0.700	0.750
A1	0.050	0.100	0.150
D	3.200	3.300	3.400
E	3.200	3.300	3.400
D1	---	1.950	---
e	---	0.650	---
ax(6)	0.300	0.350	0.400
bx(8)	0.350	0.400	0.450
L1	2.400	2.450	2.500
L2	2.150	2.200	2.250
L3	3.050	3.100	3.150
K	0.600	0.700	0.800



Top View



Bottom View



Side View